Notice of Allowability	09/941,370	9/941,370 FANG ET AL.		
	Examiner	Art Unit		
	Richard A. Booth	2812	1 (M)	
The MAILING DATE of this communication appeall claims being allowable, PROSECUTION ON THE MERITS IS nerewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT Report the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED i or other appropriate comm IGHTS. This application is	n this application. If not include unication will be mailed in due	ded e course. THIS	
1. $igtimes$ This communication is responsive to <u>the decision by the B</u>	oard of Appeals rendered o	<u>on 5/31/05</u> .		
2. ☑ The allowed claim(s) is/are <u>3,4,10 and 13</u> .				
3. $igotimes$ The drawings filed on <u>28 August 2001</u> are accepted by the	Examiner.			
 Acknowledgment is made of a claim for foreign priority unerty a) All b) Some* c) None of the: Certified copies of the priority documents have Certified copies of the priority documents have 	e been received.			
3. ☐ Copies of the certified copies of the priority do			ation from the	
International Bureau (PCT Rule 17.2(a)).				
* Certified copies not received:				
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the re	equirements	
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give			NOTICE OF	
6. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.			
(a) I including changes required by the Notice of Draftspers	son's Patent Drawing Revie	w (PTO-948) attached		
1) hereto or 2) to Paper No./Mail Date				
(b) including changes required by the attached Examiner' Paper No./Mail Date	s Amendment / Comment o	or in the Office action of		
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t	.84(c)) should be written on the header according to 37 C	the drawings in the front (not tl FR 1.121(d).	ne back) of	
 DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT 	osit of BIOLOGICAL MAT FOR THE DEPOSIT OF BI	ERIAL must be submitted. OLOGICAL MATERIAL.	Note the	
Attachment(s)	_			
1. Notice of References Cited (PTO-892)		5. Notice of Informal Patent Application (PTO-152)		
2. Notice of Draftperson's Patent Drawing Review (PTO-948)		6. ☐ Interview Summary (PTO-413), Paper No./Mail Date		
 Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 		s Amendment/Comment		
4. Examiner's Comment Regarding Requirement for Deposit		s Statement of Reasons for A	llowance	
of Biological Material	9. 🗌 Other	-· /		
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Application No.

Applicant(s)

Application/Control Number: 09/941,370 Page 2

Art Unit: 2812

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

Claims 1-2 have been cancelled.

New claim 13 has been added as follows:

- --13. A method for fabricating a memory device on a silicon substrate, the method comprising the steps of:
- (a) providing a portion of a dual gate oxide in a periphery area of the memory device;
- (b) simultaneously providing a dual gate oxide in a core area of the memory device and completing the dual gate oxide in the periphery area, wherein the dual gate oxide in the core area forms an interface between the oxide and the silicon substrate; and
- (c) strengthening the interface by providing a nitrification process in both the core area and periphery area of the memory device subsequent to steps (a) and (b), thereby improving the reliability of the dual gate oxide in the core area;
- (d) depositing a layer of type-1 polysilicon in both the core area and periphery area of the memory device;

Application/Control Number: 09/941,370

Art Unit: 2812

Page 3

(e) depositing a layer of oxide nitride oxide over the layer of type-1 polysilicon; and

(f) removing the layer of oxide nitride oxide and a portion of the layer of type-1 polysilicon from the periphery area of the memory device.—

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Richard A. Booth whose telephone number is (571) 272-1668. The examiner can normally be reached on Monday-Thursday from 7:30-6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Lebentritt can be reached on (571) 272-1873. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Richard A. Booth Primary Examiner Art Unit 2812